

**Amendments to the Specification:**

Please add, beginning at page 4, after line 26, the following new paragraph:

B1

Fig. 5 is a flow diagram of a method according to an embodiment of the invention.

Please add, beginning at page 7, between lines 27 and 28, the following new paragraphs:

B2

Fig. 5 is a flow diagram of a method according to an embodiment of the invention. The flow diagram summarizes many of the steps discussed above without adding new steps to those discussed above. Several of the blocks of the flow diagram include reference numbers that refers to elements of Figures 3 – 4D.

The method includes:

- digging trenches in the substrate 1 (step 20);
- forming insulating area 11 in the trenches (step 22);
- forming the protective layer 12 (step 24);
- forming the spacer 14 (step 26);
- implanting dopants to form N-well 15 (step 28);
- implanting dopants to form region 16 (step 30);
- implanting another active area with dopants of another type (step 32);
- removing the spacer 14 (step 34); and
- forming the conductive gate 18 on the active area (step 36).